

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S77	8	("20020137334" "20030024826" "20030049939" "20040020520" "6334983" "6460554" "6508197" "6647993").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/21 16:23
S78	1165	134/ 200.ccls.	US-PGPUB; USPAT; USOCR	OR	ON	2008/11/21 17:15
S79	1209	134/ 200.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:15
S80	191	134/ 200.ccls. and ((high-pressure) or (high near2 pressure))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:16
S81	6	134/ 200.ccls. and ((high-pressure) or (high near2 pressure)) and MPa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:17
S82	14502	(semiconductor or substrate or crystal or LCD or wafer) and ((high-pressure) or (high near2 pressure)) and MPa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:19
S83	11448	(semiconductor or substrate or crystal or LCD or wafer) and (clean\$3 or dry\$3 or wash\$3 or flush\$3 or rins\$4) and ((high- pressure) or (high near2 pressure)) and MPa	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:20

S84	4053	(semiconductor or substrate or crystal or LCD or wafer) and (clean\$3 or dry\$3 or wash\$3 or flush\$3 or rins\$4) and ((high-pressure) or (high near2 pressure)) and MPa and \$5critical	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:20
S85	1350	(semiconductor or substrate or crystal or LCD or wafer) with (clean\$3 or dry\$3 or wash\$3 or flush\$3 or rins\$4) and ((high-pressure) or (high near2 pressure)) and MPa and \$5critical	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:21
S86	7075	(semiconductor or substrate or crystal or LCD or wafer) with (clean\$3 or dry\$3 or wash\$3 or flush\$3 or rins\$4) and ((high-pressure) or (high near2 pressure)) and (torr or atm or bar or psi or MPa) and \$5critical	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:23
S87	5663	(semiconductor or substrate or crystal or LCD or wafer) with (clean\$3 or dry\$3 or wash\$3 or flush\$3 or rins\$4) and ((high-pressure) or (high near2 pressure)) and (torr or atm or psi or MPa) and \$5critical	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:24
S88	4931	(semiconductor or substrate or crystal or LCD or wafer) with (clean\$3 or dry\$3 or wash\$3 or flush\$3 or rins\$4) and ((high-pressure) or (high near2 pressure)) and (Mtorr or atm or psi or MPa) and \$5critical	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:25

S89	1609	(semiconductor or substrate or crystal or LCD or wafer) with (clean\$3 or dry\$3 or wash\$3 or flush\$3 or rins\$4) and ((high-pressure) or (high near2 pressure)) same (Mtorr or atm or psi or MPa) and \$5critical	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2008/11/21 17:25
S92	1	("4994301").PN.	USPAT; USOCR	OR	OFF	2008/11/22 02:18

11/22/2008 3:57:21 PM

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